

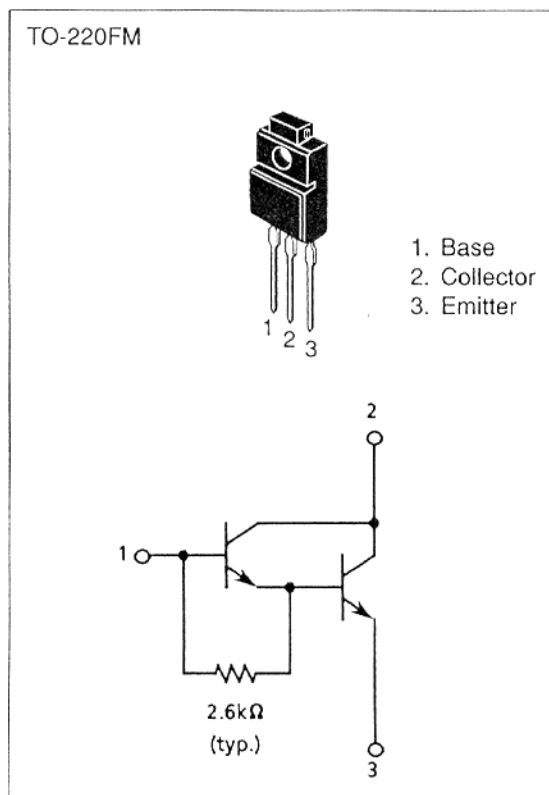
2SD2102

Silicon NPN Triple Diffused
Low Frequency Power Amplifier

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	60	V
Collector to emitter voltage	V _{CEO}	60	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _C	4	A
Collector peak current	i _{C(peak)}	8	A
Collector power dissipation	P _C	2	W
	P _C ⁻¹	25	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note: 1. Value at T_C = 25°C.



Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	V _{(BR)CBO}	60	—	—	V	I _C = 0.1 mA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	60	—	—	V	I _C = 25 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	7	—	—	V	I _E = 50 mA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	10	μA	V _{CB} = 50 V, I _E = 0
	I _{CEO}	—	—	10		V _{CE} = 50 V, R _{BE} = ∞
DC current transfer ratio	h _{FE}	1000	—	20000		V _{CE} = 3 V, I _C = 2 A ^{*1}
Collector to emitter saturation voltage	V _{CE(sat)1}	—	—	1.5	V	I _C = 2 A, I _B = 4 mA ^{*1}
	V _{CE(sat)2}	—	—	3.0		I _C = 4 A, I _B = 40 mA ^{*1}

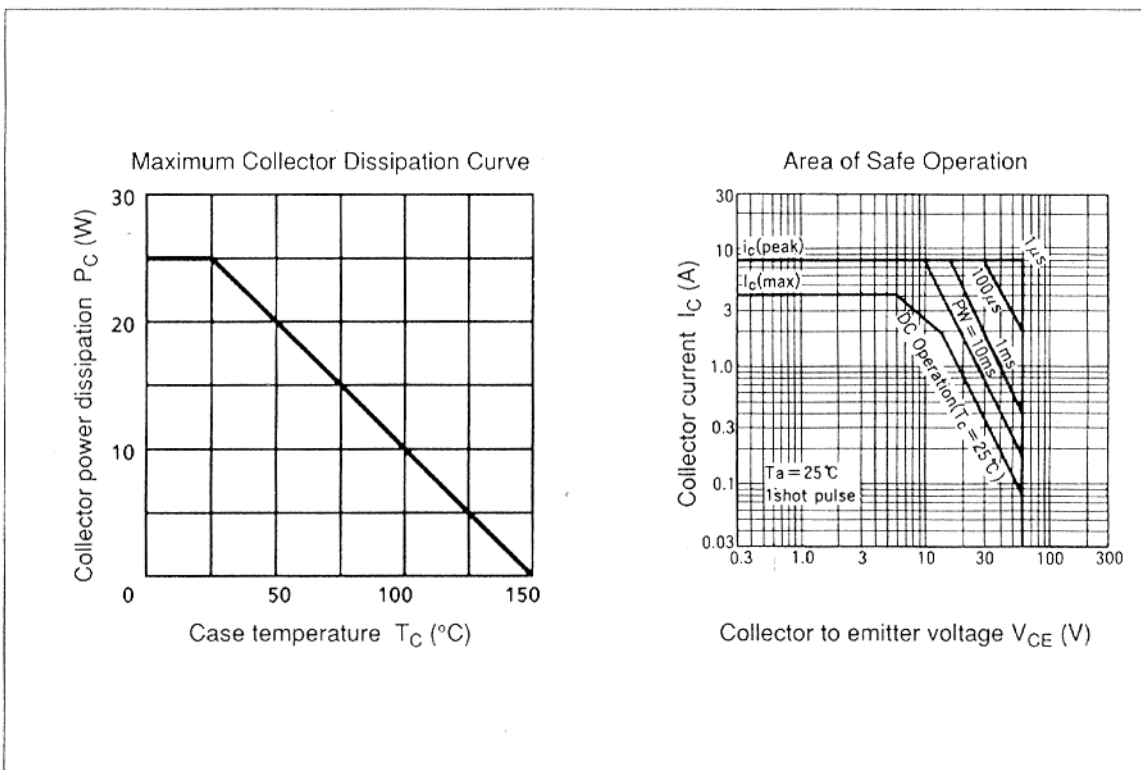
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Electrical Characteristics (Ta = 25°C) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 2\text{ A}, I_B = 4\text{ mA}^*1$
	$V_{BE(sat)2}$	—	—	3.5		$I_C = 4\text{ A}, I_B = 40\text{ mA}^*1$

Note: 1. Pulse Test.

See switching characteristic curve of 2SD1558.



2SD2102

